

# ON Semiconductor

## Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

To learn more about onsemi™, please visit our website at  
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# MMBT3906L, SMMBT3906L

## General Purpose Transistor

### PNP Silicon

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	–40	Vdc
Collector–Base Voltage	$V_{CBO}$	–40	Vdc
Emitter–Base Voltage	$V_{EBO}$	–5.0	Vdc
Collector Current – Continuous	$I_C$	–200	mAdc
Collector Current – Peak (Note 3)	$I_{CM}$	–800	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	–65 to +150	$^\circ\text{C}$

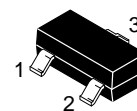
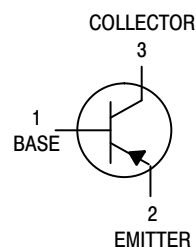
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR–5 =  $1.0 \times 0.75 \times 0.062$  in.
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.
3. Reference SOA curve.



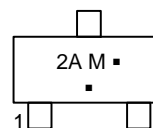
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SOT–23 (TO–236)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



2A = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT3906LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
MMBT3906LT3G	SOT–23 (Pb–Free)	10,000 / Tape & Reel
SMMBT3906LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
SMMBT3906LT3G	SOT–23 (Pb–Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT3906L, SMGBT3906L

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = -1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	-40	-	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = -10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	-40	-	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = -10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	-5.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = -30 Vdc, V <sub>EB</sub> = -3.0 Vdc)	I <sub>BL</sub>	-	-50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = -30 Vdc, V <sub>EB</sub> = -3.0 Vdc)	I <sub>CEX</sub>	-	-50	nAdc

## ON CHARACTERISTICS (Note 4)

DC Current Gain (I <sub>C</sub> = -0.1 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -50 mAdc, V <sub>CE</sub> = -1.0 Vdc) (I <sub>C</sub> = -100 mAdc, V <sub>CE</sub> = -1.0 Vdc)	H <sub>FE</sub>	60 80 100 60 30	- - 300 - -	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -1.0 mAdc) (I <sub>C</sub> = -50 mAdc, I <sub>B</sub> = -5.0 mAdc)	V <sub>CE(sat)</sub>	- -	-0.25 -0.4	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = -10 mAdc, I <sub>B</sub> = -1.0 mAdc) (I <sub>C</sub> = -50 mAdc, I <sub>B</sub> = -5.0 mAdc)	V <sub>BE(sat)</sub>	-0.65 -	-0.85 -0.95	Vdc

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = -10 mAdc, V <sub>CE</sub> = -20 Vdc, f = 100 MHz)	f <sub>T</sub>	250	-	MHz
Output Capacitance (V <sub>CB</sub> = -5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	4.5	pF
Input Capacitance (V <sub>EB</sub> = -0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	-	10	pF
Input Impedance (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	2.0	12	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	10	X 10 <sup>-4</sup>
Small–Signal Current Gain (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	100	400	-
Output Admittance (I <sub>C</sub> = -1.0 mAdc, V <sub>CE</sub> = -10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	3.0	60	μmhos
Noise Figure (I <sub>C</sub> = -100 μAdc, V <sub>CE</sub> = -5.0 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	NF	-	4.0	dB

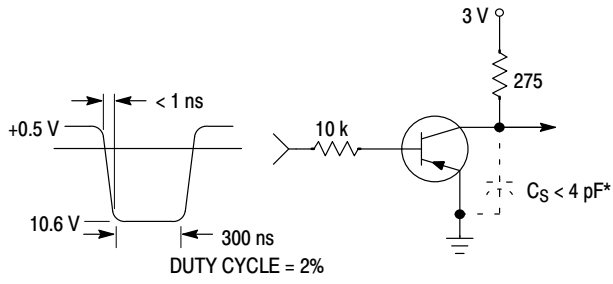
## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = -3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc, I <sub>C</sub> = -10 mAdc, I <sub>B1</sub> = -1.0 mAdc)	t <sub>d</sub>	-	35	ns
Rise Time		t <sub>r</sub>	-	35	
Storage Time	(V <sub>CC</sub> = -3.0 Vdc, I <sub>C</sub> = -10 mAdc, I <sub>B1</sub> = I <sub>B2</sub> = -1.0 mAdc)	t <sub>s</sub>	-	225	ns
Fall Time		t <sub>f</sub>	-	75	

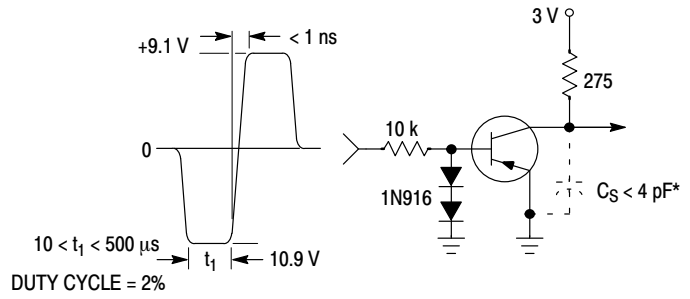
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

# MMBT3906L, SMMBT3906L



**Figure 1. Delay and Rise Time Equivalent Test Circuit**

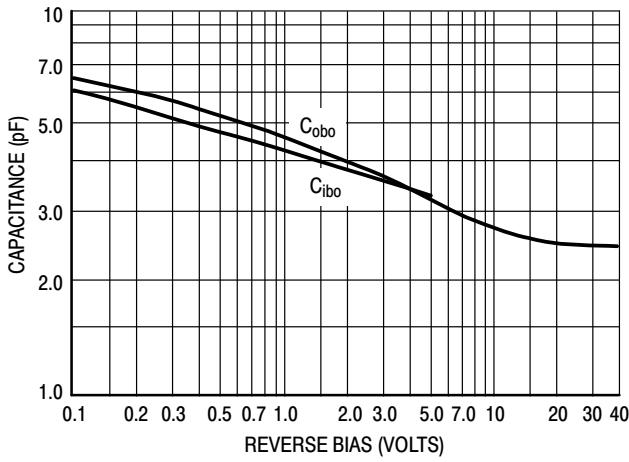


**Figure 2. Storage and Fall Time Equivalent Test Circuit**

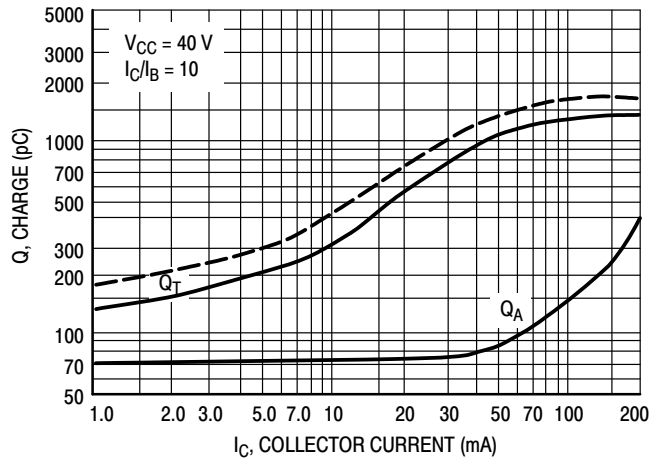
\* Total shunt capacitance of test jig and connectors

## TYPICAL TRANSIENT CHARACTERISTICS

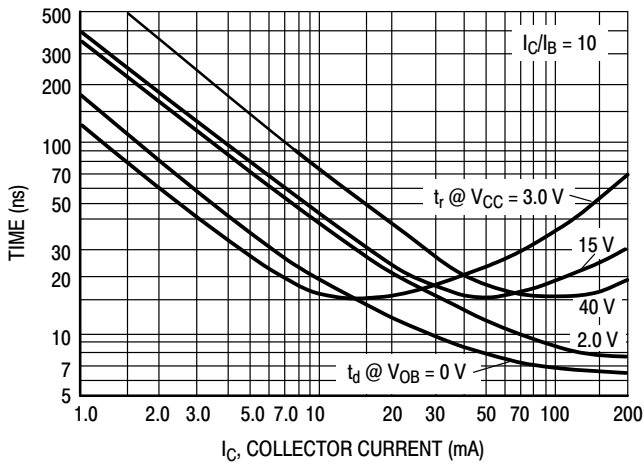
—  $T_J = 25^\circ\text{C}$   
 - - -  $T_J = 125^\circ\text{C}$



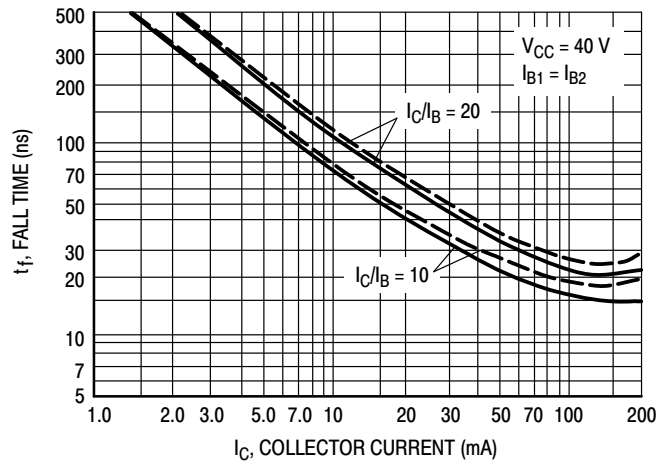
**Figure 3. Capacitance**



**Figure 4. Charge Data**



**Figure 5. Turn-On Time**



**Figure 6. Fall Time**

# MMBT3906L, SMMBT3906L

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

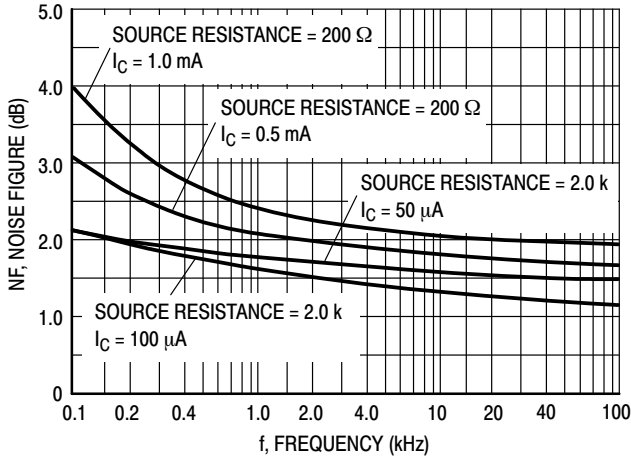


Figure 7.

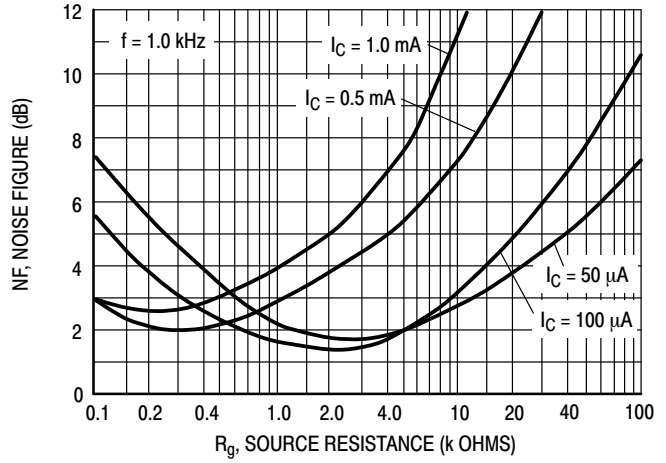


Figure 8.

## h PARAMETERS

( $V_{CE} = -10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

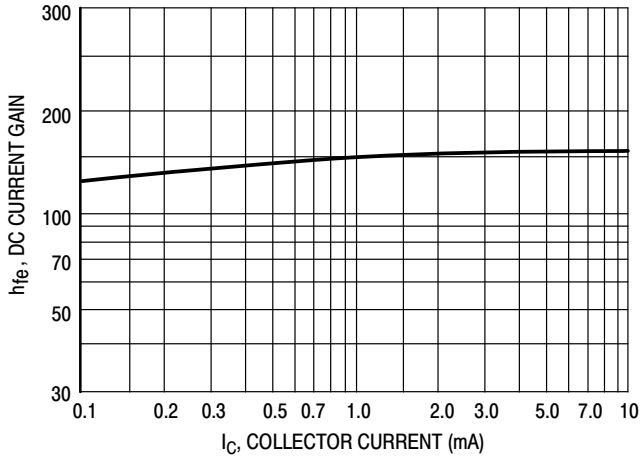


Figure 9. Current Gain

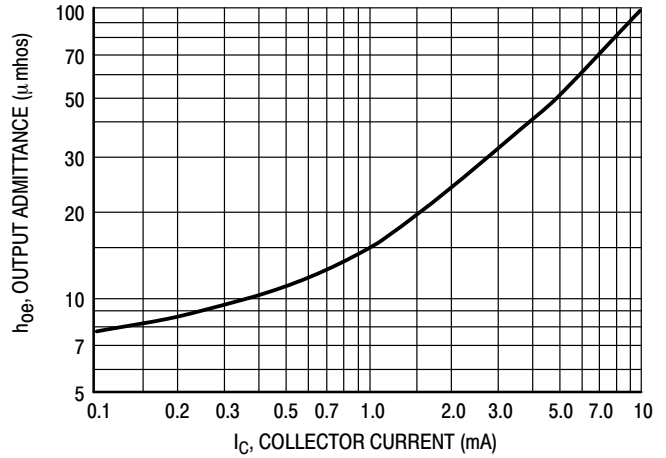


Figure 10. Output Admittance

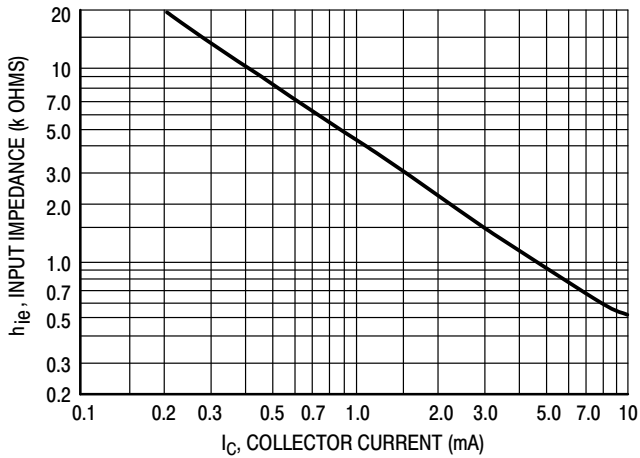


Figure 11. Input Impedance

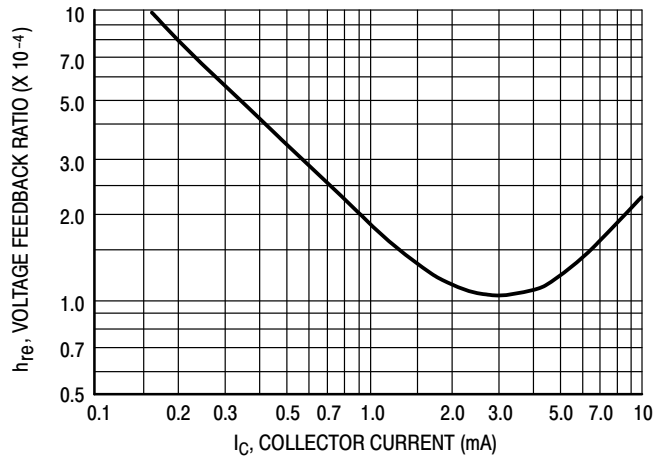


Figure 12. Voltage Feedback Ratio

# MMBT3906L, SMMBT3906L

## TYPICAL STATIC CHARACTERISTICS

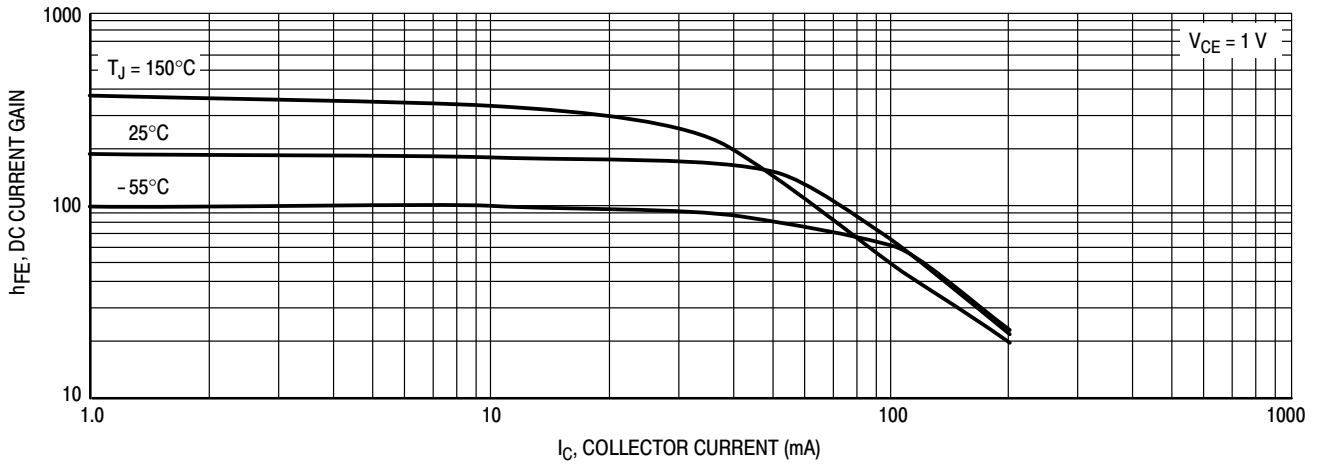


Figure 13. DC Current Gain

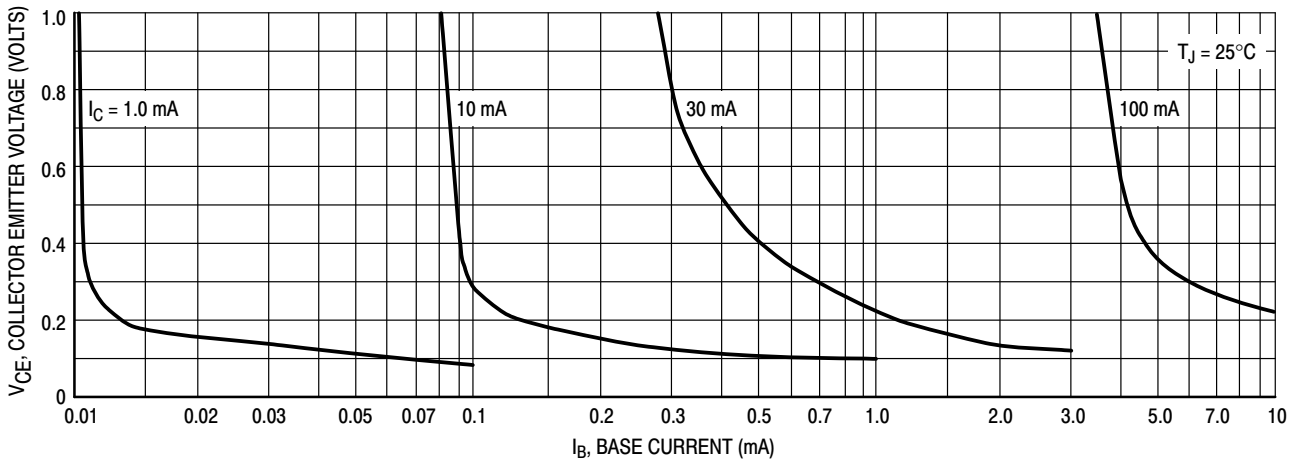
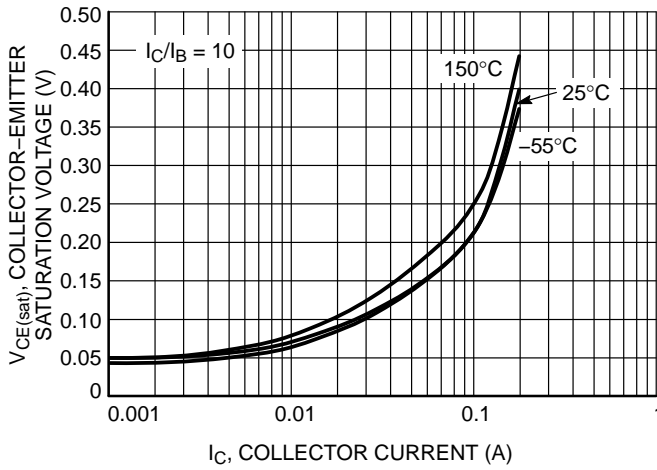
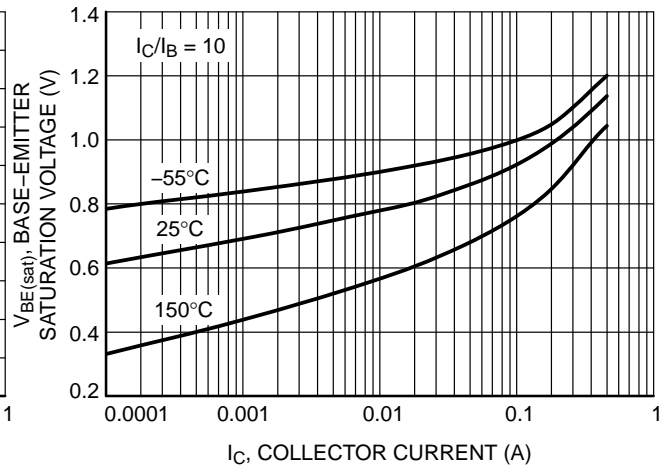


Figure 14. Collector Saturation Region

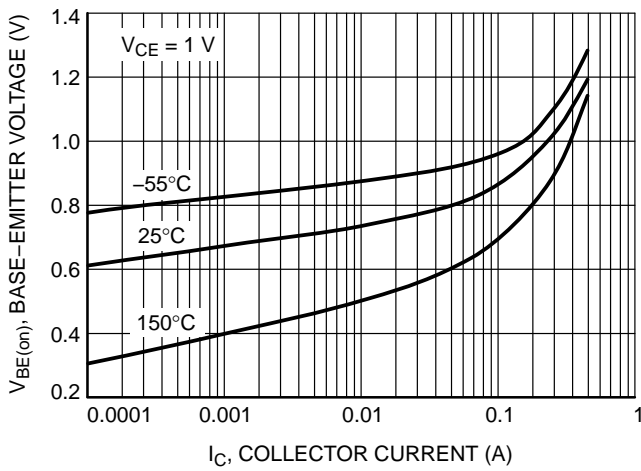
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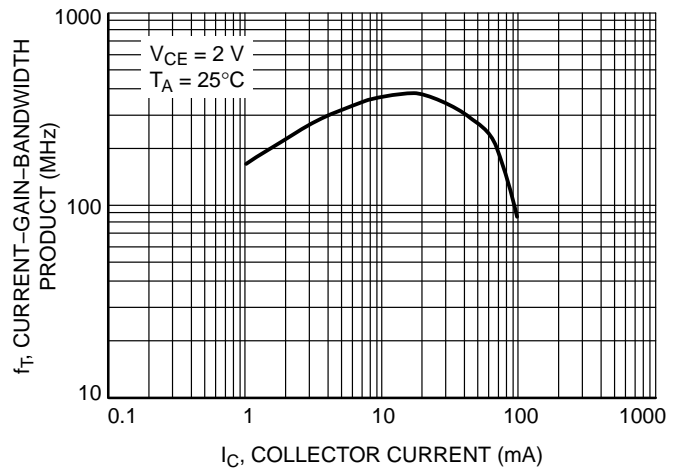
**Figure 15. Collector Emitter Saturation Voltage vs. Collector Current**



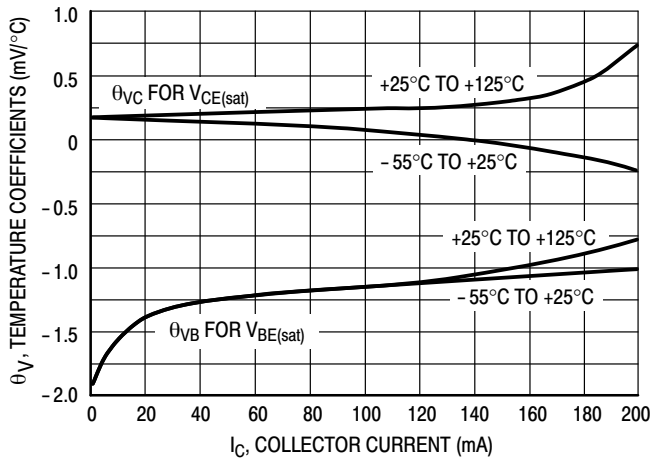
**Figure 16. Base Emitter Saturation Voltage vs. Collector Current**



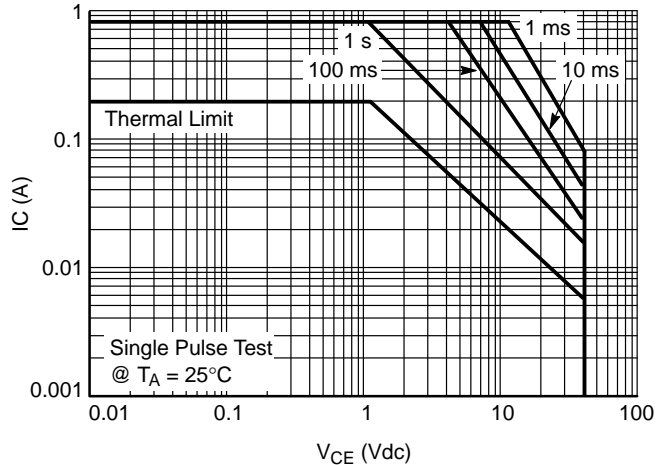
**Figure 17. Base Emitter Voltage vs. Collector Current**



**Figure 18. Current Gain Bandwidth vs. Collector Current**



**Figure 19. Temperature Coefficients**

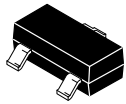


**Figure 20. Safe Operating Area**

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

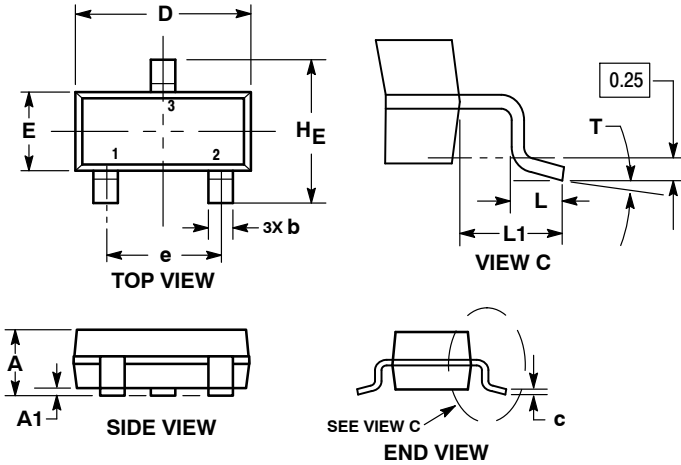
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### SOT-23 (TO-236) CASE 318-08 ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

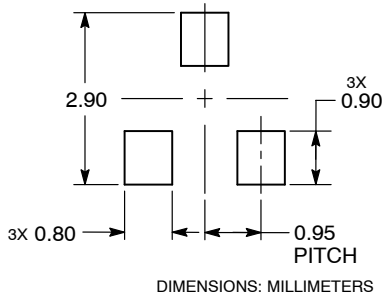


NOTES:

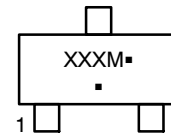
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

### RECOMMENDED SOLDERING FOOTPRINT



### GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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